

SKCD 24 C 065 I4F



CAL-DIODE

$I_F = 50 \text{ A}^{1)}$
 $V_{RRM} = 650 \text{ V}$
 Size: $4,9 \times 4,9 \text{ mm}^2$

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Features

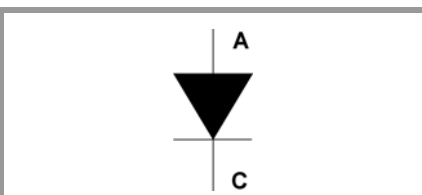
- low forward voltage drop combined with a low temperature dependence
- easy paralleling due to a small forward voltage spread
- very soft recovery behavior
- small switching losses
- high ruggedness

Typical Applications*

- freewheeling diode for IGBT

Footnotes

¹⁾ Nominal IGBT I_F rating, verified by design and characterization



SKCD

| Absolute Maximum Ratings | | | |
|--------------------------|---|------------------------------------|------------------|
| Symbol | Conditions | Values | Unit |
| V_{RRM} | $T_j = 25 \text{ }^\circ\text{C}$, $I_R = 0.06 \text{ mA}$ | 650 | V |
| I_{FSM} | 10 ms | $T_j = 25 \text{ }^\circ\text{C}$ | A |
| | sin 180° | $T_j = 150 \text{ }^\circ\text{C}$ | A |
| i^2t | $T_j = 150 \text{ }^\circ\text{C}$, $t_p = 10 \text{ ms}$, sin 180° | 1058 | A ² s |
| T_{jmax} | | 175 | °C |

| Electrical Characteristics | | | | | |
|----------------------------|---|------|-------|-------|------|
| Symbol | Conditions | min. | typ. | max. | Unit |
| $I_{F(AV)}$ | $T_c = 80 \text{ }^\circ\text{C}$, $T_j = 175 \text{ }^\circ\text{C}$, $F_r = PI/2$, Semitrans Assembly; $R_{th(j-c)} = 1.2 \text{ K/W}$ | | 43 | | A |
| I_R | $T_j = 25 \text{ }^\circ\text{C}$, $V_{RRM} = 650 \text{ V}$ | | | 0.06 | mA |
| | $T_j = 150 \text{ }^\circ\text{C}$, $V_{RRM} = 650 \text{ V}$ | | | 20.00 | mA |
| V_F | $T_j = 25 \text{ }^\circ\text{C}$, $I_F = 39 \text{ A}$ | | 1.30 | 1.62 | V |
| | $T_j = 150 \text{ }^\circ\text{C}$, $I_F = 39 \text{ A}$ | | 1.24 | 1.56 | V |
| | $T_j = 175 \text{ }^\circ\text{C}$, $I_F = 39 \text{ A}$ | | 1.18 | 1.49 | V |
| $V_{(TO)}$ | $T_j = 150 \text{ }^\circ\text{C}$ | | 0.85 | 0.99 | V |
| r_T | $T_j = 150 \text{ }^\circ\text{C}$ | | 10.09 | 14.62 | mΩ |
| $V_{(TO)}$ | $T_j = 175 \text{ }^\circ\text{C}$ | | 0.78 | 0.95 | V |
| | $T_j = 175 \text{ }^\circ\text{C}$ | | 10.25 | 13.85 | mΩ |

| Dynamic Characteristics | | | | | |
|-------------------------|--|------|------|------|------|
| Symbol | Conditions | min. | typ. | max. | Unit |
| E_{rr} | $T_j = 25 \text{ }^\circ\text{C}$, 60 A, 400 V, 900 A/μs | | 0.3 | | mJ |
| E_{rr} | $T_j = 150 \text{ }^\circ\text{C}$, 60 A, 400 V, 900 A/μs | | 1.1 | | mJ |
| Q_{rr} | $T_j = 25 \text{ }^\circ\text{C}$, 60 A, 400 V, 900 A/μs | | 2.4 | | μC |
| Q_{rr} | $T_j = 150 \text{ }^\circ\text{C}$, 60 A, 400 V, 900 A/μs | | 6.1 | | μC |
| I_{rrm} | $T_j = 25 \text{ }^\circ\text{C}$, 60 A, 400 V, 900 A/μs | | 31 | | A |
| I_{rrm} | $T_j = 150 \text{ }^\circ\text{C}$, 60 A, 400 V, 900 A/μs | | 44 | | A |

| Thermal Characteristics | | | | | |
|-------------------------|------------|------|------|------|------|
| Symbol | Conditions | min. | typ. | max. | Unit |
| T_j | | -40 | | 175 | °C |
| T_{stg} | | -40 | | 175 | °C |
| T_{solder} | 10 min. | | | 250 | °C |
| T_{solder} | 5 min. | | | 320 | °C |

| Mechanical Characteristics | | | |
|----------------------------|---------------|----------------------------|-----------------|
| Symbol | Conditions | Values | Unit |
| Raster size | | 4,9 x 4,9 | mm ² |
| Area total | | 24,01 | mm ² |
| Anode | Metallization | bondable (Al) | |
| Cathode | Metallization | solderable (Ag/Ni) | |
| Wire bond | | Al, typ. diameter = 300 μm | |
| Package | | 150 mm wafer frame | |
| Chips / Package | | 620 | pcs |

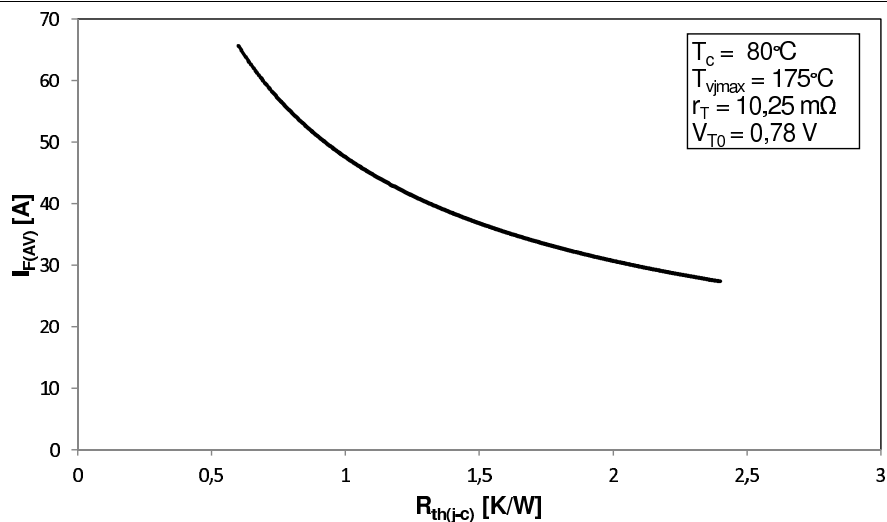
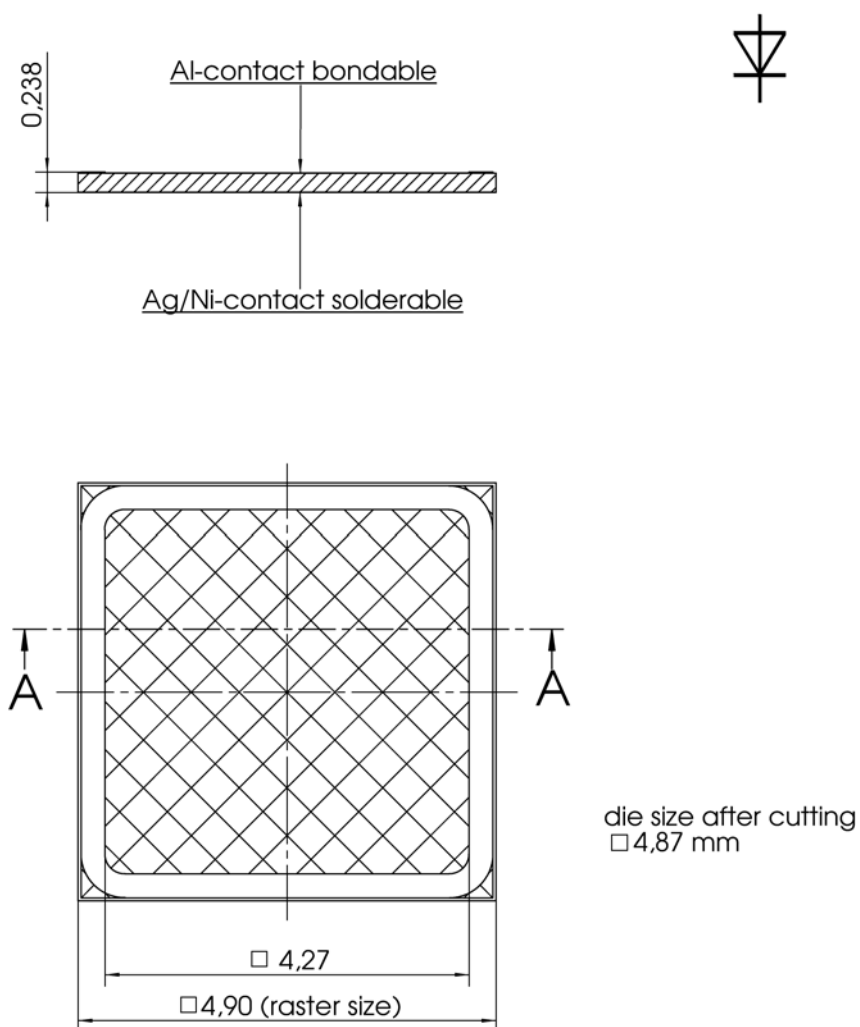


Fig. 1: Rated current vs. thermal resistance



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.